

Title (en)

Tantalum-aluminum oxide coatings for semiconductor devices

Title (de)

Tantalum-aluminium oxid Beschichtung für Halbleitervorrichtungen

Title (fr)

Revêtements d'oxide de Tantalum-aluminium pour dispositifs à semiconducteur

Publication

EP 0845839 A1 19980603 (EN)

Application

EP 97309473 A 19971125

Priority

US 75863096 A 19961127

Abstract (en)

An active semiconductor device (10) includes a coating (14) comprising an oxide of tantalum and aluminum. The coating may function as an AR coating or as a passivation coating for a semiconductor laser device. Applications to ICs and optical devices are described.

IPC 1-7

H01S 3/025; **H01L 21/00**

IPC 8 full level

G02B 1/11 (2015.01); **G02B 1/113** (2015.01); **H01L 33/06** (2010.01); **H01L 33/30** (2010.01); **H01S 5/00** (2006.01); **H01S 5/028** (2006.01); **H01S 5/022** (2006.01)

CPC (source: EP US)

H01S 5/0282 (2013.01 - EP US); **H01S 5/02234** (2021.01 - EP US); **H01S 5/0287** (2013.01 - EP US)

Citation (search report)

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